Attorney Docket No.: 0180197

RECEIVED CENTRAL FAX CENTER

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

OCT 2 1 2004

In re Application of: Bin Yu

Serial No.: 09/826,472

Filed: April 4, 2001

For: Method of Fabricating a Semiconductor

Device Having a Nitride/High-k/Nitride Gate Dielectric Stack by Atomic Layer Deposition (ALD) and a Device Thereby

Formed

Art Unit: 2812

Examiner: Pompey, Ron Everett

RESPONSE TO FINAL OFFICE ACTION

Mail Stop AF Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir/Madam:

This is in response to the *Final Office Action* dated September 22, 2004 in the above-referenced patent application. Please enter and consider the following remarks.